



High-end Power Semiconductor Manufacturer

KP2450A 8500V

Phase Control Thyristor

- High power cycling capability
- Low on-state and switching losses
- Designed for traction and industrial applications



Mean on-state current	I_{TAV}	2450 A
Repetitive peak off-state voltage	V_{DRM}	8500 V
Repetitive peak reverse voltage	V_{RRM}	
Turn-off time	t_q	550 μ s
T_{vj} , °C		25 – 125

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	2450	$T_c=70$ °C, half-sine wave	
I_{TRMS}	RMS on-state current	A	3840	$T_c=70$ °C, half-sine wave	
I_{TSM}	Surge on-state current	kA	64	$V_D = V_R = 0$ V	$t_p = 10$ ms, $T_{vj} = 125$ °C, sine half wave, after surge
			/	$V_R = 0.6 \cdot V_{RRM}$	$t_p = 10$ ms, $T_{vj} = 125$ °C, sine half wave, after surge
I^2t	Safety factor	$A^2s \cdot 10^3$	20500	$V_D = V_R = 0$ V	$t_p = 10$ ms, $T_{vj} = 125$ °C, sine half wave, after surge
			/	$V_R = 0.6 \cdot V_{RRM}$	$t_p = 10$ ms, $T_{vj} = 125$ °C, sine half wave, after surge
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	8500	$f = 50$ Hz, $t_p = 10$ ms, $t_{p1} = 250\mu$ s, $T_{vj} = 25...125$ °C	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	8500	$t_p = 10$ ms, $f = 5$ Hz, $T_{vj} = 25...125$ °C	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j = T_{j\max}$; Gate open	

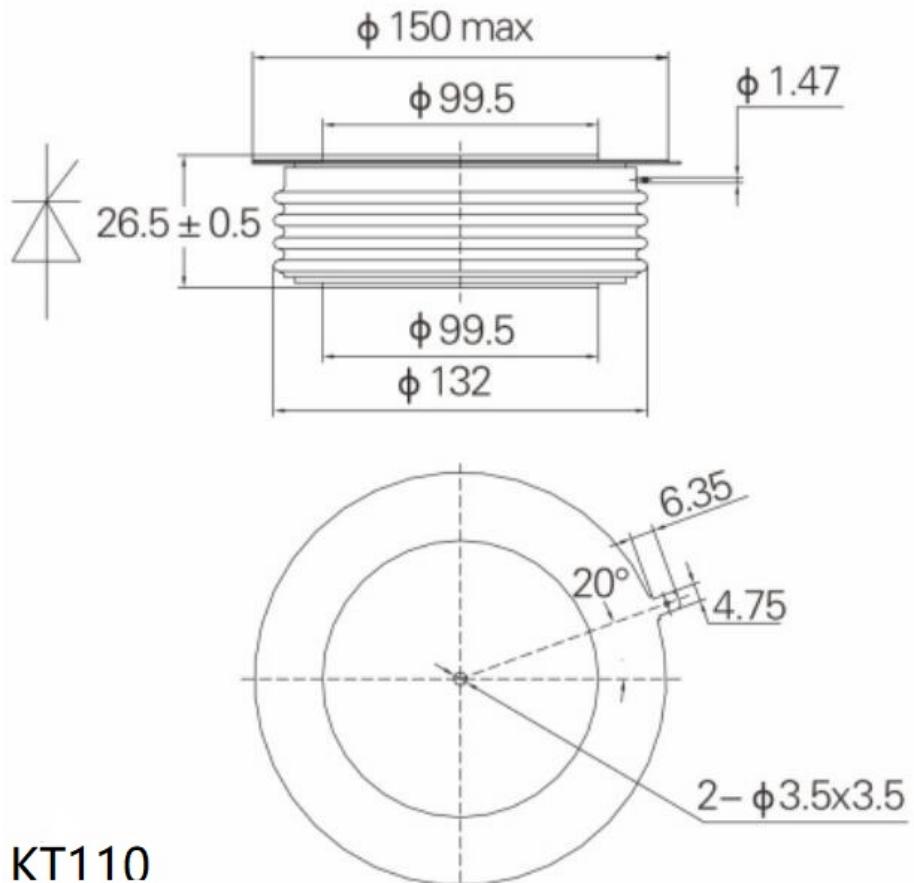
TRIGGERING				
I _{FGM}	Peak forward gate current	A	10	T _j =T _{j max}
V _{RGM}	Peak reverse gate voltage	V	10	
P _G	Gate power dissipation	W	3	
SWITCHING				
(dI _T /dt) _{crit}	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/μs	1000	T _{vj} = 125 °C, I _{TRM} = 2000 A, V _D ≤ 0.67·V _{DRM} , I _{FG} = 2 A, t _r = 0.5 μs
THERMAL				
T _{stg}	Storage temperature	°C	-40-140	
T _j	Operating junction temperature	°C	125	
MECHANICAL				
F	Mounting force	kN	81-108	
a	Acceleration	m/s ²	50 100	Device unclamped Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{TM}	Peak on-state voltage, max	V	1.72	I _T = 1500 A, T _{vj} = 125 °C	
V _{T(TO)}	On-state threshold voltage, max	V	1.09	I _T = 800 A - 3000 A, T _{vj} = 125 °C	
r _T	On-state slope resistance, max	mΩ	0.42		
I _L	Latching current, max	mA	500	T _{vj} =25°C	
I _H	Holding current, max	mA	160	T _{vj} =25°C	
BLOCKING					
I _{DRM} , I _{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	600	V _{DRM} , T _{vj} = 125 °C	
(dv _D /dt) _{crit}	Critical rate of rise of off-state voltage ¹⁾	V/μs	3000	Exp. to 0.67·V _{DRM} , T _{vj} = 125 °C	
TRIGGERING					
V _{GT}	Gate trigger direct voltage, max	V	2.60	T _{vj} =25°C	
I _{GT}	Gate trigger direct current, max	mA	400	T _{vj} =25°C	
V _{GD}	Gate non-trigger direct voltage, min	V	0.30	V _D = 0.4·V _{DRM} , T _{vjmax} = 125 °C dv/dt = 1000 V/μs	
I _{GD}	Gate non-trigger direct current, min	mA	10.00		
SWITCHING					
t _{gd}	Delay time	μs	3.00	T _{vj} = 25 °C, V _D = 0.4·V _{DRM} , I _{FG} = 2 A, t _r = 0.5 μs	
t _q	Turn-off time ²⁾	μs	550	T _{vj} = 125 °C, I _{TRM} = 2000 A, V _R = 200 V, dI _T /dt = -1.5 A/μs, V _D ≤ 0.67·V _{DRM} , dv _D /dt = 20 V/μs	
Q _{rr} I _{rrM}	Total recovered charge, max Peak reverse recovery current, max	μAs A	7000 95	T _{vj} = 125 °C, I _{TRM} = 2000 A, V _R = 200 V, dI _T /dt = -1.5 A/μs	

THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	K/kW	5.7	Direct current	Double side cooled
R_{thjc-A}			11.4		Anode side cooled
R_{thjc-K}			11.4		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	K/kW	1	Double-side cooled	
MECHANICAL					
W	Weight, typ	g	2900		
D_s	Surface creepage distance	mm	56		
D_a	Air strike distance	mm	22		

OVERALL DIMENSIONS



All dimensions in millimeters